# **Analog Multiplexer/ Demultiplexer**

# **High-Performance Silicon-Gate CMOS**

The MC74LVX8051 utilizes silicon–gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF leakage currents. This analog multiplexer/demultiplexer controls analog voltages that may vary across the complete power supply range (from  $V_{CC}$  to GND).

The LVX8051 is similar in pinout to the high-speed HC4051A and the metal-gate MC14051B. The Channel-Select inputs determine which one of the Analog Inputs/Outputs is to be connected, by means of an analog switch, to the Common Output/Input. When the Enable pin is HIGH, all analog switches are turned off.

The Channel-Select and Enable inputs are compatible with standard CMOS outputs; with pull-up resistors they are compatible with LSTTL outputs.

This device has been designed so that the ON resistance  $(R_{on})$  is more linear over input voltage than  $R_{on}$  of metal-gate CMOS analog switches.

#### **Features**

- Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Analog Power Supply Range  $(V_{CC} GND) = 2.5$  to 6.0 V
- Digital (Control) Power Supply Range  $(V_{CC} GND) = 2.5$  to 6.0 V
- Improved Linearity and Lower ON Resistance Than Metal–Gate Counterparts
- Low Noise
- In Compliance With the Requirements of JEDEC Standard No. 7A
- Chip Complexity: LVX8051 184 FETs or 46 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



#### ON Semiconductor®

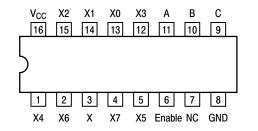
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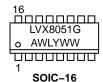


SOIC-16 D SUFFIX CASE 751B TSSOP-16 DT SUFFIX CASE 948F

#### **PIN ASSIGNMENT**



#### MARKING DIAGRAMS





TSSOP-16

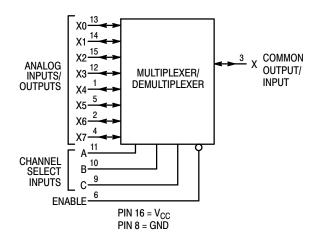
LVX8051 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

# ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.



#### **FUNCTION TABLE - MC74LVX8051**

Conti	rol Inp			
		Selec	t	
Enable	С	В	Α	ON Channels
L	L	L	L	X0
L	L	L	Н	X1
L	L	Н	L	X2
L	L	Н	Н	Х3
L	Н	L	L	X4
L	Н	L	Н	X5
L	Н	Н	L	X6
L	Н	Н	Н	X7
Н	X	Χ	Χ	NONE

X = Don't Care

# LOGIC DIAGRAM MC74LVX8051 Single-Pole, 8-Position Plus Common Off

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Positive DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>IS</sub>	Analog Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>in</sub>	Digital Input Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
I	DC Current, Into or Out of Any Pin	± 20	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C TSSOP Package: -6.1 mW/°C from 65° to 125°C This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage (Referenced to GND)	2.5	6.0	V
V <sub>IS</sub>	Analog Input Voltage	0.0	V <sub>CC</sub>	V
V <sub>in</sub>	Digital Input Voltage (Referenced to GND)	GND	V <sub>CC</sub>	V
V <sub>IO</sub> *	Static or Dynamic Voltage Across Switch		1.2	V
T <sub>A</sub>	Operating Temperature Range, All Package Types	<b>–</b> 55	+ 85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Channel Select or Enable Inputs)			ns/V
	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

<sup>\*</sup>For voltage drops across switch greater than 1.2 V (switch on), excessive V<sub>CC</sub> current may be drawn; i.e., the current out of the switch may contain both V<sub>CC</sub> and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

# **DC CHARACTERISTICS — Digital Section** (Voltages Referenced to GND)

			V <sub>CC</sub>	Guara			
Symbol	Parameter	Condition	V	-55 to 25°C	≤85°C	≤125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage, Channel-Select or Enable Inputs	R <sub>on</sub> = Per Spec	2.5 3.0 4.5 5.5	1.50 2.10 3.15 3.85	1.50 2.10 3.15 3.85	1.50 2.10 3.15 3.85	٧
V <sub>IL</sub>	Maximum Low–Level Input Voltage, Channel–Select or Enable Inputs	R <sub>on</sub> = Per Spec	2.5 3.0 4.5 5.5	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	٧
I <sub>in</sub>	Maximum Input Leakage Current, Channel-Select or Enable Inputs	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	Channel Select, Enable and V <sub>IS</sub> = V <sub>CC</sub> or GND; V <sub>IO</sub> = 0 V	5.5	4.0	40	160	μΑ

# DC ELECTRICAL CHARACTERISTICS (Analog Section)

		V <sub>CC</sub>		Guara	nteed Lin	nit	
Symbol	Parameter	Test Conditions	V	–55 to 25°C	≤85°C	≤125°C	Unit
R <sub>on</sub>	Maximum "ON" Resistance	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = V_{CC} \text{ to GND}$ $ I_S  \le 10.0 \text{ mA (Figures 1, 2)}$	3.0 4.5 5.5	40 30 25	45 32 28	50 37 30	Ω
		$V_{in} = V_{IL}$ or $V_{IH}$ $V_{IS} = V_{CC}$ or GND (Endpoints) $ I_S  \le 10.0$ mA (Figures 1, 2)	3.0 4.5 5.5	30 25 20	35 28 25	40 35 30	
$\Delta R_{on}$	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = 1/2 (V_{CC} - GND)$ $ I_S  \le 10.0 \text{ mA}$	3.0 4.5 5.5	15 8.0 8.0	20 12 12	25 15 15	Ω
l <sub>off</sub>	Maximum Off–Channel Leakage Current, Any One Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} \text{ or GND};$ Switch Off (Figure 3)	5.5	0.1	0.5	1.0	μΑ
	Maximum Off–Channel Leakage Current, Common Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} \text{ or GND};$ Switch Off (Figure 4)	5.5	0.2	2.0	4.0	
I <sub>on</sub>	Maximum On–Channel Leakage Current, Channel–to–Channel	$V_{in} = V_{IL}$ or $V_{IH}$ ; Switch-to-Switch = $V_{CC}$ or GND; (Figure 5)	5.5	0.2	2.0	4.0	μΑ

# AC CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 3 \text{ ns}$ )

			v <sub>cc</sub>	Guara	Guaranteed Limit			
Symbol	Parameter		V	–55 to 25°C	≤85°C	≤125°C	Unit	
t <sub>PLH</sub> ,	Maximum Propagation Delay, Channel-Select to	o Analog Output	2.5	30	35	40	ns	
t <sub>PHL</sub>	(Figure 9)		3.0	20	25	30		
			4.5	15	18	22		
			5.5	15	18	20		
t <sub>PLH</sub> ,	Maximum Propagation Delay, Analog Input to A	nalog Output	2.5	4.0	6.0	8.0	ns	
$t_{PHL}$	(Figure 10)		3.0	3.0	5.0	6.0		
			4.5	1.0	2.0	2.0		
			5.5	1.0	2.0	2.0		
$t_{PLZ}$ ,	Maximum Propagation Delay, Enable to Analog	Output	2.5	30	35	40	ns	
$t_{PHZ}$	(Figure 11)		3.0	20	25	30		
			4.5	15	18	22		
			5.5	15	18	20		
$t_{PZL},$	Maximum Propagation Delay, Enable to Analog	Output	2.5	20	25	30	ns	
t <sub>PZH</sub>	(Figure 11)		3.0	12	14	15		
			4.5	8.0	10	12		
			5.5	8.0	10	12		
C <sub>in</sub>	Maximum Input Capacitance, Channel-Select of	r Enable Inputs		10	10	10	pF	
C <sub>I/O</sub>	Maximum Capacitance	Analog I/O		35	35	35	pF	
	(All Switches Off)	Common O/I		130	130	130		
		Feedthrough		1.0	1.0	1.0		

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Figure 13)*	45	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D$  =  $C_{PD}$   $V_{CC}^2$ f +  $I_{CC}$   $V_{CC}$ .

# ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

			V <sub>CC</sub>	Limit*	
Symbol	Parameter	Condition	V	25°C	Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response (Figure 6)	$\begin{array}{l} f_{in} = \text{1MHz Sine Wave; Adjust } f_{in} \text{ Voltage to Obtain} \\ \text{0dBm at V}_{OS}; \text{ Increase } f_{in} \text{ Frequency Until dB} \\ \text{Meter Reads } -3 \text{ dB;} \\ \text{R}_{L} = 50 \ \Omega, \ C_{L} = 10 \text{ pF} \end{array}$		80 80 80	MHz
_	Off-Channel Feedthrough Isolation (Figure 7)	$f_{in}$ = Sine Wave; Adjust $f_{in}$ Voltage to Obtain 0dBm at V <sub>IS</sub> $f_{in}$ = 10 kHz, $R_L$ = 600 $\Omega$ , $C_L$ = 50 pF	3.0 4.5 5.5	-50 -50 -50	dB
		$f_{in}$ = 1.0 MHz, $R_L$ = 50 $\Omega$ , $C_L$ = 10 pF	3.0 4.5 5.5	-37 -37 -37	
_	Feedthrough Noise. Channel–Select Input to Common I/O (Figure 8)	$V_{in} \le$ 1MHz Square Wave (t <sub>r</sub> = t <sub>f</sub> = 6ns); Adjust R <sub>L</sub> at Setup so that I <sub>S</sub> = 0 A; Enable = GND $R_L = 600 \ \Omega$ , $C_L = 50 \ pF$	3.0 4.5 5.5	25 105 135	mV <sub>PP</sub>
		$R_L = 10 \text{ k}\Omega, C_L = 10 \text{ pF}$	3.0 4.5 5.5	35 145 190	
THD	Total Harmonic Distortion (Figure 14)	$\begin{aligned} f_{in} &= 1 \text{ kHz}, \text{ R}_L = 10 \text{ k}\Omega, \text{ C}_L = 50 \text{ pF} \\ \text{THD} &= \text{THD}_{measured} - \text{THD}_{source} \\ & \text{V}_{IS} = 2.0 \text{ V}_{PP} \text{ sine wave} \\ & \text{V}_{IS} = 4.0 \text{ V}_{PP} \text{ sine wave} \\ & \text{V}_{IS} = 5.0 \text{ V}_{PP} \text{ sine wave} \end{aligned}$	3.0 4.5 5.5	0.10 0.08 0.05	%

<sup>\*</sup>Limits not tested. Determined by design and verified by qualification.

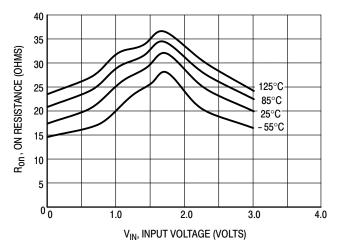


Figure 1a. Typical On Resistance,  $V_{CC} = 3.0 \text{ V}$ 

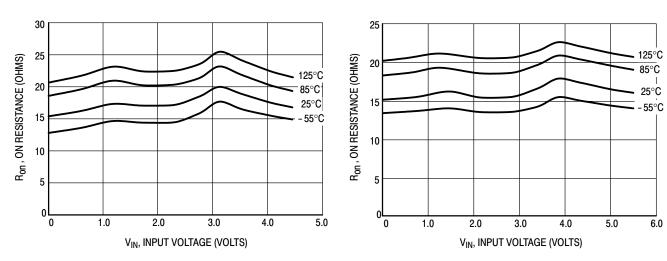


Figure 1b. Typical On Resistance,  $V_{CC} = 4.5 \text{ V}$ 

Figure 1c. Typical On Resistance,  $V_{CC} = 5.5 \text{ V}$ 

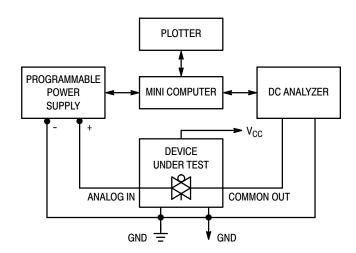


Figure 2. On Resistance Test Set-Up

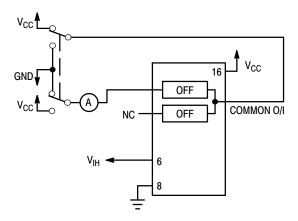


Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

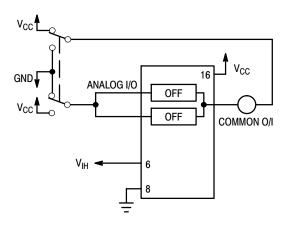


Figure 4. Maximum Off Channel Leakage Current, Common Channel, Test Set-Up

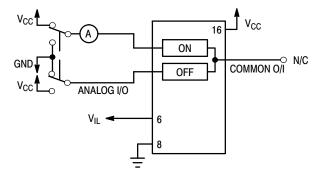


Figure 5. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

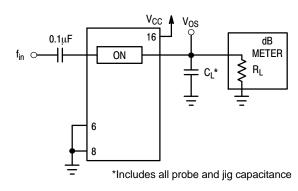


Figure 6. Maximum On Channel Bandwidth, Test Set-Up

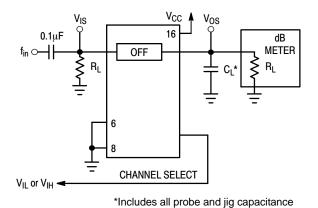
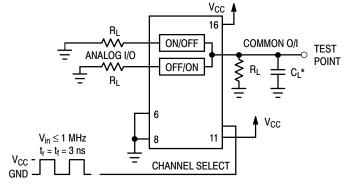


Figure 7. Off Channel Feedthrough Isolation, Test Set-Up



\*Includes all probe and jig capacitance

Figure 8. Feedthrough Noise, Channel Select to Common Out, Test Set-Up

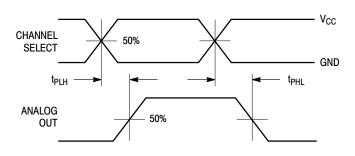
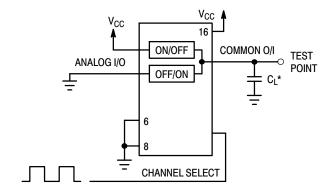


Figure 9a. Propagation Delays, Channel Select to Analog Out



\*Includes all probe and jig capacitance

Figure 9b. Propagation Delay, Test Set-Up Channel Select to Analog Out

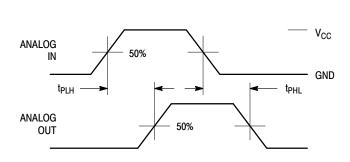


Figure 10a. Propagation Delays, Analog In to Analog Out

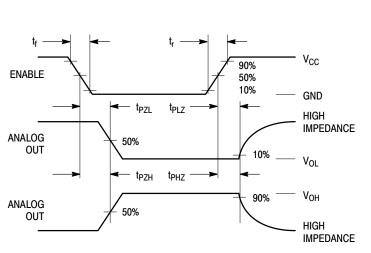
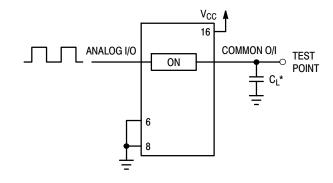


Figure 11a. Propagation Delays, Enable to Analog Out



\*Includes all probe and jig capacitance

Figure 10b. Propagation Delay, Test Set-Up Analog In to Analog Out

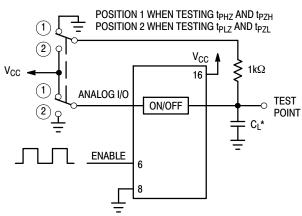
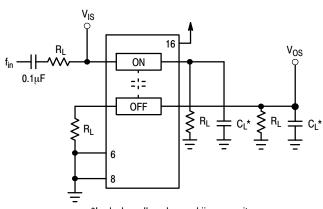


Figure 11b. Propagation Delay, Test Set-Up
Enable to Analog Out



\*Includes all probe and jig capacitance

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up

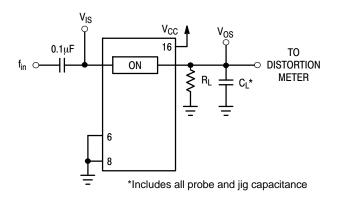


Figure 14a. Total Harmonic Distortion, Test Set-Up

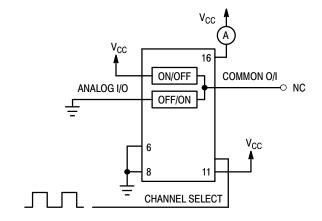


Figure 13. Power Dissipation Capacitance, Test Set-Up

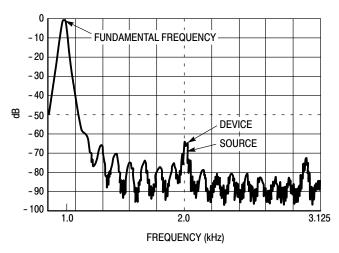


Figure 14b. Plot, Harmonic Distortion

# **APPLICATIONS INFORMATION**

The Channel Select and Enable control pins should be at  $V_{CC}$  or GND logic levels.  $V_{CC}$  being recognized as a logic high and GND being recognized as a logic low. In this example:

$$V_{CC} = +5V = logic \ high$$
  
 $GND = 0V = logic \ low$ 

The maximum analog voltage swing is determined by the supply voltage  $V_{CC}$ . The positive peak analog voltage should not exceed  $V_{CC}$ . Similarly, the negative peak analog voltage should not go below GND. In this example, the difference between  $V_{CC}$  and GND is five volts. Therefore, using the configuration of Figure 15, a maximum analog signal of five volts peak—to—peak can be controlled. Unused analog inputs/outputs may be left floating (i.e., not

connected). However, tying unused analog inputs and outputs to  $V_{CC}$  or GND through a low value resistor helps minimize crosstalk and feedthrough noise that may be picked up by an unused switch.

Although used here, balanced supplies are not a requirement. The only constraints on the power supplies are that:

$$V_{CC} - GND = 2$$
 to 6 volts

When voltage transients above  $V_{CC}$  and/or below GND are anticipated on the analog channels, external Germanium or Schottky diodes  $(D_x)$  are recommended as shown in Figure 16. These diodes should be able to absorb the maximum anticipated current surges during clipping.

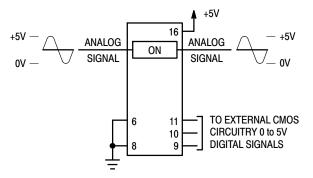


Figure 15. Application Example

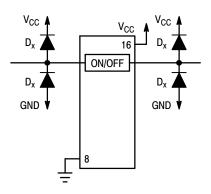
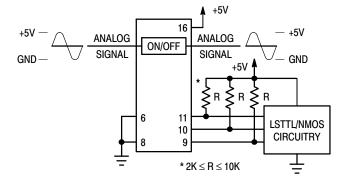
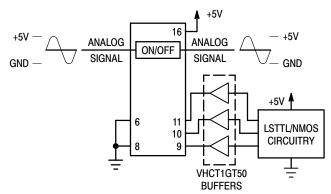


Figure 16. External Germanium or Schottky Clipping Diodes

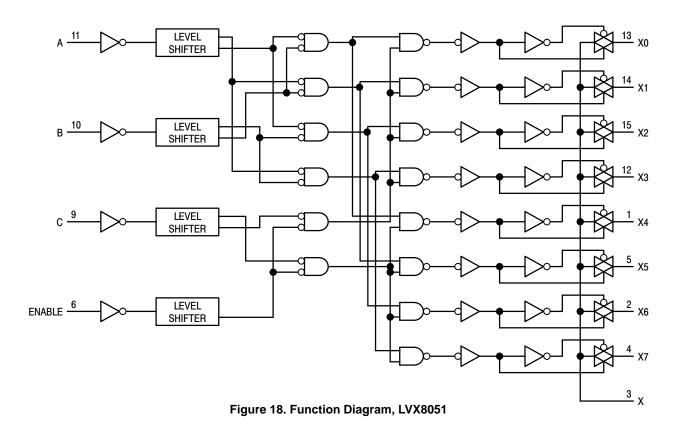


a. Using Pull-Up Resistors



b. Using HCT Interface

Figure 17. Interfacing LSTTL/NMOS to CMOS Inputs



http://onsemi.com

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LVX8051DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74LVX8051DTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74LVX8051DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





#### SOIC-16 CASE 751B-05 **ISSUE K**

**DATE 29 DEC 2006** 

- NOTES:

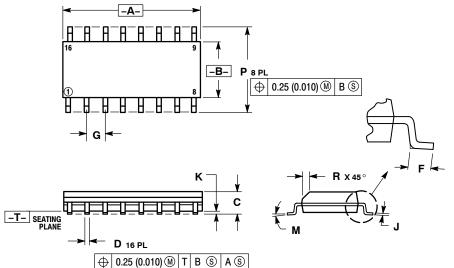
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD DESCRIPTION AND BEAUTION AND BEAUTION AND BEAUTION AND BEAUTION AND BEAUTI
- PROTRUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- MAXIMUM MOLL PRO INCLUDE DAMBAR PROTRUSION A LLOWAGE NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



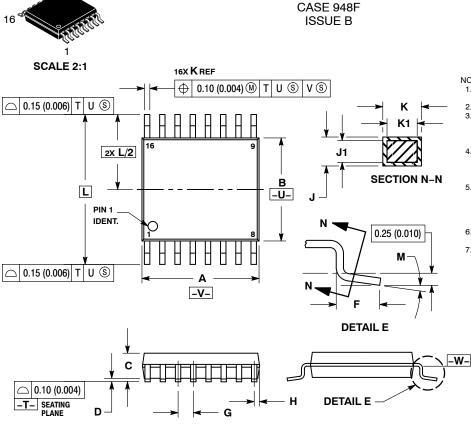
STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR		CATHODE		COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #	1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.			
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.		12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.		13.	COLLECTOR, #4	13.	BASE, #2	RECOMI	MENDED
14.	COLLECTOR		NO CONNECTION		BASE, #4	14.	EMITTER, #2	SOI DERING	FOOTPRINT*
15.	EMITTER		ANODE	15.	EMITTER, #4	15.	BASE, #1	COLDLINIG	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	8	3X
								<b>←</b> 6.	40 →
STYLE 5:		STYLE 6:		STYLE 7:					1
	DRAIN, DYE #1		CATHODE		SOURCE N-CH				16X 1.12 < ➤
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	IT)			,
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPU			. 🗀 1	16
4.	DRAIN, #2	4.		4.	GATE P-CH	.,	١	, —	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	IT)	_		
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		16X 7		
7.	DRAIN, #4		CATHODE	7.	COMMON DRAIN (OUTPU		0.58	`	
8.	DRAIN, #4	8.		8.	SOURCE P-CH	.,	0.50		
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	IT)			
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3	12.		12.	COMMON DRAIN (OUTPU				
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	-,			
14.	SOURCE, #2		ANODE	14.	COMMON DRAIN (OUTPU	IT)			
15.	GATE, #1		ANODE	15.	COMMON DRAIN (OUTPU				. PITCH
16.	SOURCE, #1		ANODE		SOURCE N-CH	-,			<u>+-+-</u>
	,								
								<b>8</b>	9 + - + -
								<b>—</b> "	ı - <b> ↑</b>
									DIMENOIONO, MILLIMETERO
									DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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TSSOP-16 WB

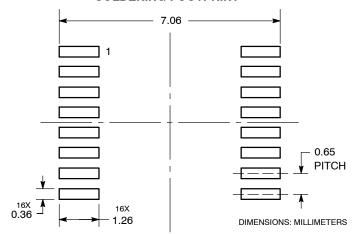
**DATE 19 OCT 2006** 

#### NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
  INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
  NOT EXCEED 0.25 (0.010) PER SIDE.
  DIMENSION K DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABILE DAMBAR
  PROTRUSION SHALL BE 0.08 (0.003) TOTAL
  IN EXCESS OF THE K DIMENSION AT
  MAXIMUM MATERIAL CONDITION.
  TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0 °	8°	0 °	8 °

#### **RECOMMENDED** SOLDERING FOOTPRINT\*



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **GENERIC MARKING DIAGRAM\***



= Specific Device Code XXXX = Assembly Location Α

= Wafer Lot L = Year = Work Week W G or • = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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